

Silicon NPN Power Transistors

2SC1880

DESCRIPTION

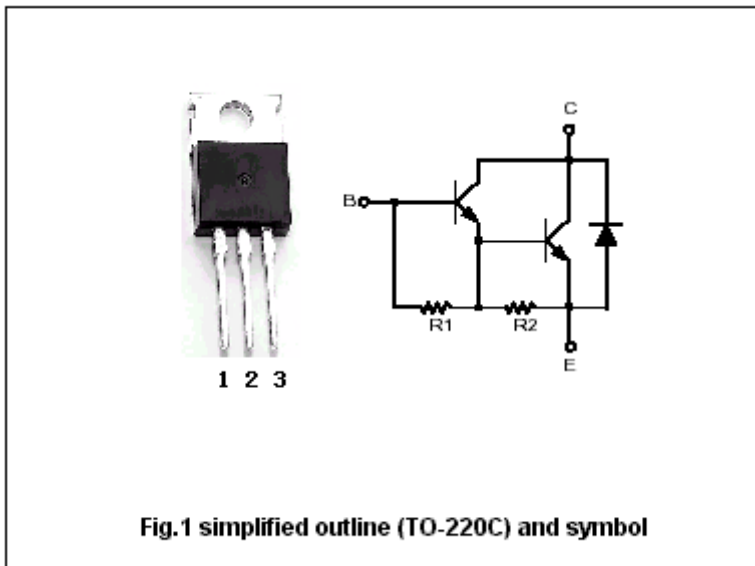
- With TO-220C package
- DARLINGTON
- High DC current gain

APPLICATIONS

- For industrial use

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	120	V
V _{CEO}	Collector-emitter voltage	Open base	120	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current-DC		2	A
I _{CM}	Collector current-Pulse		4	A
P _C	Collector power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =30mA, I _B =0	120			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA, I _E =0	120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50mA, I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A, I _B =8mA			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =100V, I _E =0			0.1	mA
I _{CEO}	Collector cut-off current	V _{CE} =100V, I _B =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =2V	1000			

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PACKAGE OUTLINE

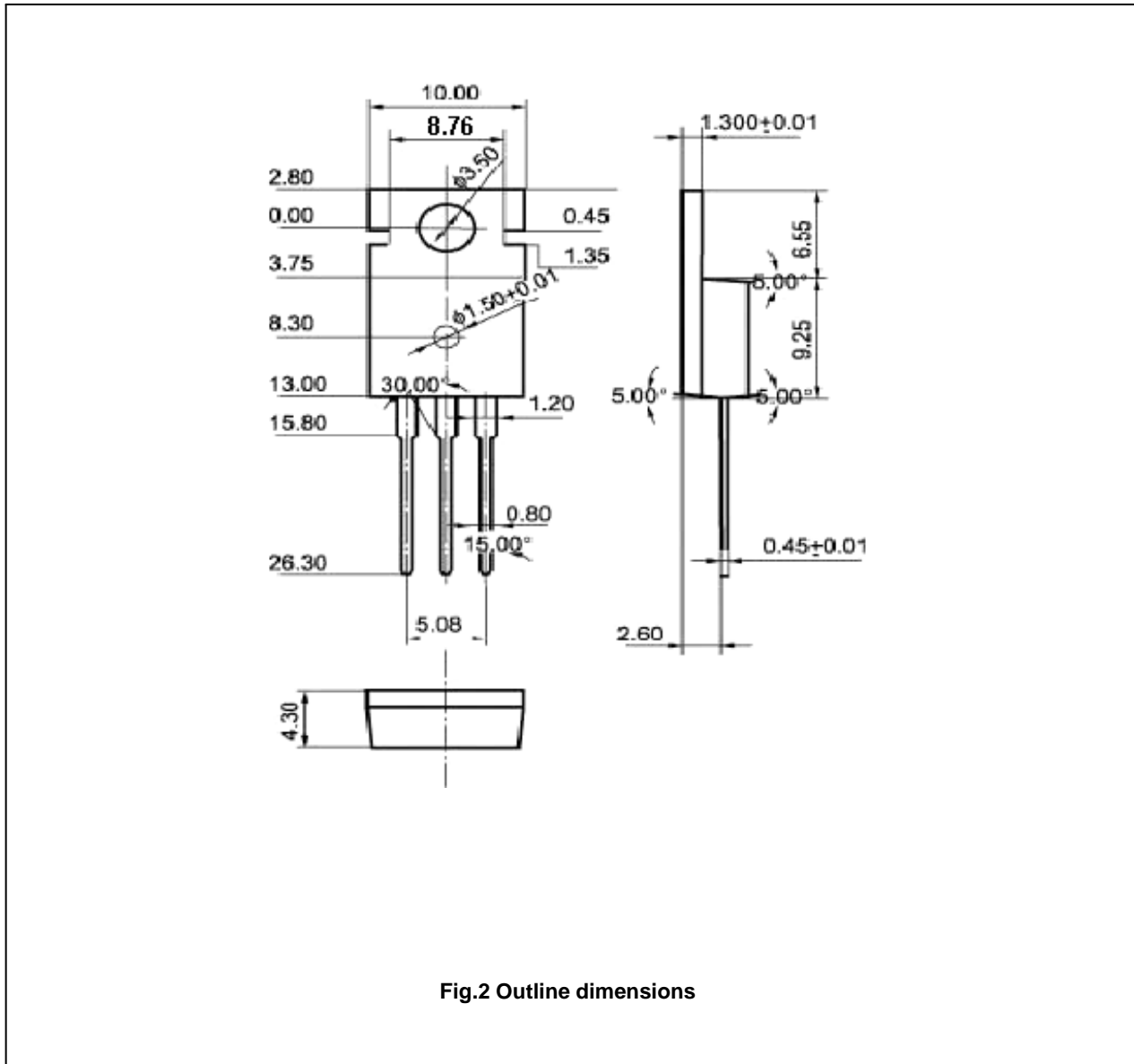


Fig.2 Outline dimensions